

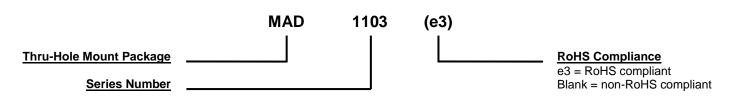
MAXIMUM RATINGS

Parameters/Test Conditions		Symbol	Value	Unit
Junction and Storage Temperature		T_J and T_{STG}	-55 to +150	°C/W
Peak Working Reverse Voltage		V_{RWM}	75	V
Repetitive Peak Forward Current (one diode)	I _{FRM}	400	mA	
Forward Surge Current	@ 8.3 ms	I _{FSM}	2	Α
	@ 8/20 μs		12	
Rated Average Power dissipation (total)		P _{M(AV)}	1500	mW
Solder Temperature @ 10 s			260	°C

MECHANICAL and PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy body meeting UL94V-0 flammability classification
- TERMINALS: Tin-lead or RoHS compliant annealed matte-tin plating solderable per MIL-STD-750 method 2026
- MARKING: MSC logo, MAD1103 or MAD1103e3 and date code. Pin #1 is to the left of the dot or indent on top of package.
- DELIVERY OPTION: Carrier tube. Consult factory for quantities
- WEIGHT: Approximately 0.997 grams
- See <u>Package Dimensions</u> on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS				
Symbol	Definition			
Ст	Total Capacitance: The total small signal capacitance between the diode terminals of a complete device.			
I_R	Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V _R .			
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current I _(BR) in the breakdown region.			
V _F	Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current.			
V _{RWM}	Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV.			

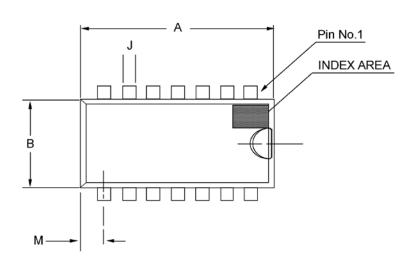
ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise stated

PART NUMBER	BREAKDOWN VOLTAGE V _(BR) @ I _(BR) =100 μA	LEAK CURF I _F T _A = 2	RENT 25 °C	LEAKAGE CURRENT I _R T _A = 150 °C		CAPACITANCE C _T @ 0 V pF	REVERSE RECOVERY TIME t _{rr}	FORWARD VOLTAGE V _F I _F = 10 mA	FORWARD VOLTAGE V_F $I_F = 100 \text{ mA}$
	MIN	MAX	@V _R	MAX	@ V _R	TYP (Note 1)	MAX	MAX	MAX

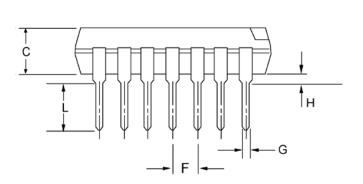
NOTE 1: Individual diode capacitance is less than 1.5 pF but will read higher between pins with the connected parallel diode array shown.

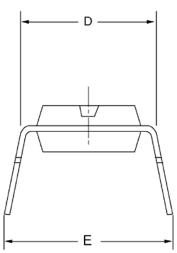


PACKAGE DIMENSIONS

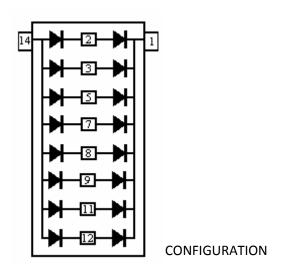


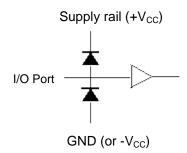
	Dimensions						
Ref.	Ir	nch	Millimeters				
	Min	Max	Min	Max			
Α	0.746	0.754	18.95	19.15			
В	0.246	0.254	6.248	6.452			
C	0.126	0.134	3.200	3.404			
D	0.300	0.325	7.619	8.255			
Е	0.320	0.370	8.128	9.398			
F	0.098	0.102	2.489	2.591			
G	0.016	0.020	0.406	0.508			
Н	0.015	0.040	0.381	1.016			
J	0.058	0.062	1.473	1.575			
L	0.121	0.129	3.073	3.277			
М	0.25	REF	0.635 REF				





CIRCUIT





STEERING DIODE APPLICATION